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November 2013

SGL50N60RUFD 600 V, 50 A Short Circuit Rated IGBT

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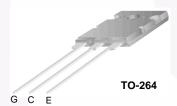
Fairchild's RUFD series of Insulated Gate Bipolar Transistors (IGBTs) provide low conduction and switching losses as well as short circuit ruggedness. The RUFD series is designed for applications such as motor control, uninterrupted power supplies (UPS) and general inverters where short circuit ruggedness is a required feature.

Features

- 50 A, 600 V, T_C = 100°C
- Low Saturation Voltage: $V_{CE}(sat) = 2.2 \text{ V} @ I_{C} = 50 \text{ A}$
- High Speed Switching
- High Input Impedance
- Short Circuit Rating

Applications

Motor Control, UPS, General Inverter.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description		Ratings	Unit
V _{CES}	Collector-Emitter Voltage		600	V
V _{GES}	Gate-Emitter Voltage		± 20	V
	Collector Current	@ T _C = 25°C	80	Α
IC	Collector Current	@ T _C = 100°C	50	Α
I _{CM (1)}	Pulsed Collector Current		150	A
	Diode Continuous Forward Current	@ T _C = 25°C	60	А
I _F	Diode Continuous Forward Current	@ T _C = 100°C	30	А
I _{FM}	Diode Maximum Forward Current		90	Α
T _{SC}	Short Circuit Withstand Time	@ T _C = 100°C	10	us
P_{D}	Maximum Power Dissipation	@ T _C = 25°C	250	W
	Maximum Power Dissipation	@ T _C = 100°C	100	W
TJ	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds		300	°C

Notes:
(1) Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction-to-Case		0.5	°C/W
$R_{\theta JC}(DIODE)$	Thermal Resistance, Junction-to-Case		1.0	°C/W
R _{0,JA}	Thermal Resistance, Junction-to-Ambient		25	°C/W

Electrical Characteristics of the IGBT $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	racteristics					
BV _{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V, } I_{C} = 250 \text{ uA}$	600			V
ΔB _{VCES} / ΔT _J	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0 V, I _C = 1 mA		0.6		V/°C
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$			250	uA
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$			± 100	nA
On Chai	racteristics					
$V_{GE(th)}$	G-E Threshold Voltage	$Ic = 50 \text{ mA}, V_{CE} = V_{GE}$	5.0	6.0	8.5	V
/ / / / / / / / / / / / / / / / / /	Collector to Emitter	I _C = 50 A, V _{GE} = 15 V		2.2	2.8	V
V _{CE(sat)}	Saturation Voltage	I _C = 80 A, V _{GE} = 15 V		2.5		V
•	c Characteristics					
C _{ies}	Input Capacitance	V _{CE} =30 V, V _{GE} = 0 V,		3311		pF
C _{oes}	Output Capacitance	f = 1 MHz		399		pF
C _{res}	Reverse Transfer Capacitance	1 = 1 10112		139		pF
	ng Characteristics Turn-On Delay Time			26		ns
t _{d(on)}	Rise Time			89		ns
	Turn-Off Delay Time	V 300 V I 50 Λ		66	100	ns
t _{d(off)}	Fall Time	$V_{CC} = 300 \text{ V}, I_{C} = 50 \text{ A},$ $R_{G} = 5.9 \Omega, V_{GE} = 15 \text{ V},$		118	200	ns
E _{on}	Turn-On Switching Loss	Inductive Load, $T_C = 25^{\circ}C$		1.68		mJ
E _{off}	Turn-Off Switching Loss			1.03		mJ
E _{ts}	Total Switching Loss			2.71	3.8	mJ
t _{d(on)}	Turn-On Delay Time			28		ns
t _r	Rise Time			91		ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 300 \text{ V}, I_{C} = 50 \text{ A},$		68	110	ns
t _f	Fall Time	$R_G = 5.9 \Omega, V_{GE} = 15 V,$	/	261	400	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 125°C		1.7		mJ
E _{off}	Turn-Off Switching Loss			2.31		mJ
E _{ts}	Total Switching Loss			4.01	5.62	mJ
T _{sc}	Short Circuit Withstand Time	V _{CC} = 300 V, V _{GE} = 15 V @ T _C = 100°C	10			us
Q_g	Total Gate Charge	V = 300 V I = - 50 A		145	210	nC
Q_{ge}	Gate-Emitter Charge	$V_{CE} = 300 \text{ V}, I_{C} = 50 \text{ A},$ $V_{GE} = 15 \text{ V}$		25	35	nC
Q _{gc}	Gate-Collector Charge	VGE = 10 V		70	100	nC
Le	Internal Emitter Inductance	Measured 5mm from PKG		18		nΗ

Electrical Characteristics of DIODE $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
V _{FM}	Diode Forward Voltage	I _F = 30 A	$T_C = 25^{\circ}C$		1.9	2.8	V
		IF = 30 A	T _C = 100°C		1.8	1.8	
t _{rr}	Diode Peak Reverse Recovery I _F		$T_C = 25^{\circ}C$		70	100	nc
			T _C = 100°C		140		ns
1		I _F = 30 A,	$T_C = 25^{\circ}C$		6	7.8	Α
'rr		ent $di_F/dt = 200 \text{ A/us}$ $T_C = 100$	T _C = 100°C	-	8		Α
Q _{rr}	Diode Reverse Recovery Charge		$T_C = 25^{\circ}C$		200	360	nC
			$T_{\rm C} = 100^{\circ}{\rm C}$		580		110

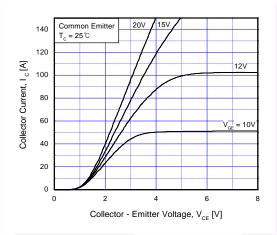


Fig 1. Typical Output Characteristics

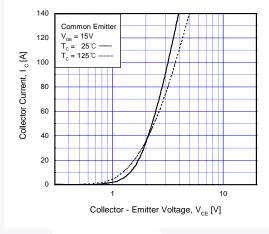


Fig 2. Typical Saturation Voltage Characteristics

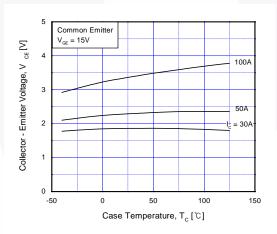


Fig 3. Saturation Voltage vs. Case
Temperature at Variant Current Level

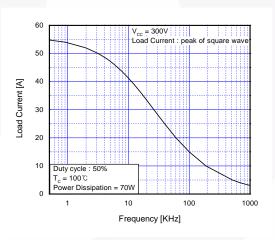


Fig 4. Load Current vs. Frequency

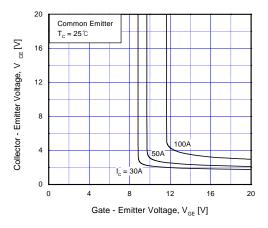


Fig 5. Saturation Voltage vs. V_{GE}

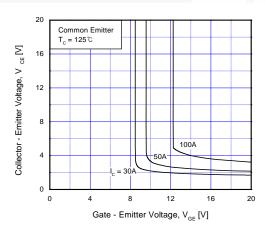


Fig 6. Saturation Voltage vs. V_{GE}

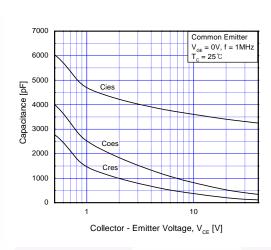


Fig 7. Capacitance Characteristics

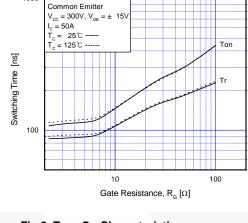


Fig 8. Turn-On Characteristics vs.
Gate Resistance

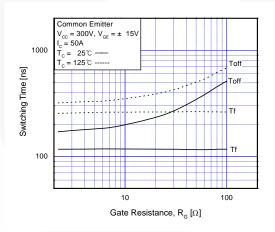


Fig 9. Turn-Off Characteristics vs. Gate Resistance

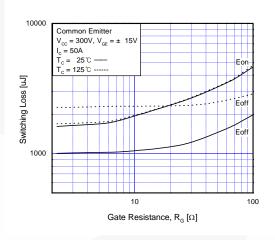


Fig 10. Switching Loss vs. Gate Resistance

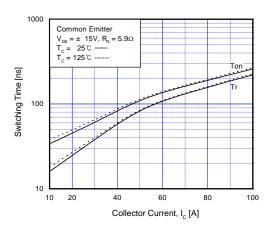


Fig 11. Turn-On Characteristics vs. Collector Current

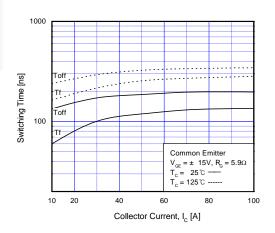
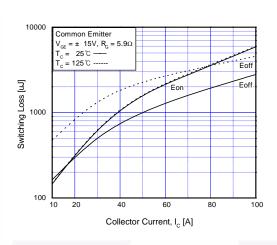


Fig 12. Turn-Off Characteristics vs. Collector Current



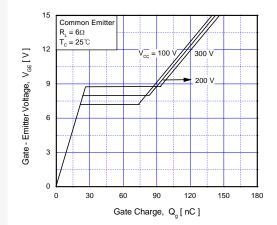
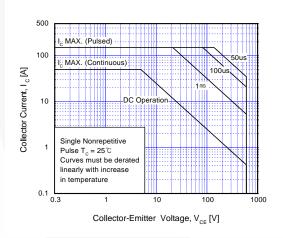


Fig 13. Switching Loss vs. Collector Current

Fig 14. Gate Charge Characteristics



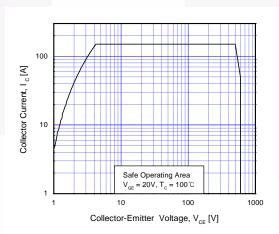


Fig 15. SOA Characteristics

Fig 16. Turn-Off SOA Characteristics

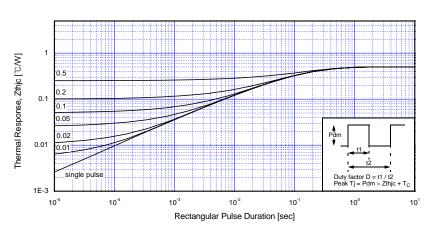


Fig 17. Transient Thermal Impedance of IGBT

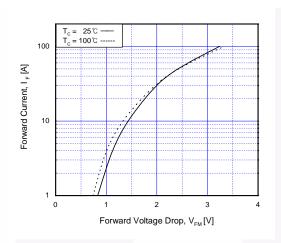


Fig 18. Forward Characteristics

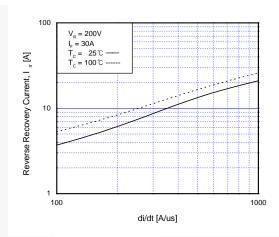


Fig 19. Reverse Recovery Current

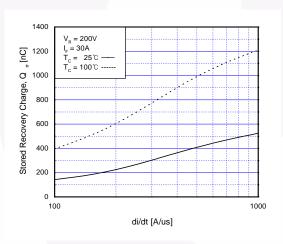


Fig 20. Stored Charge

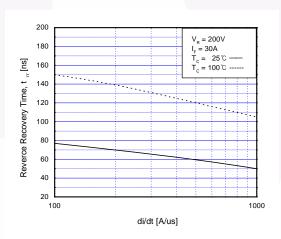


Fig 21. Reverse Recovery Time

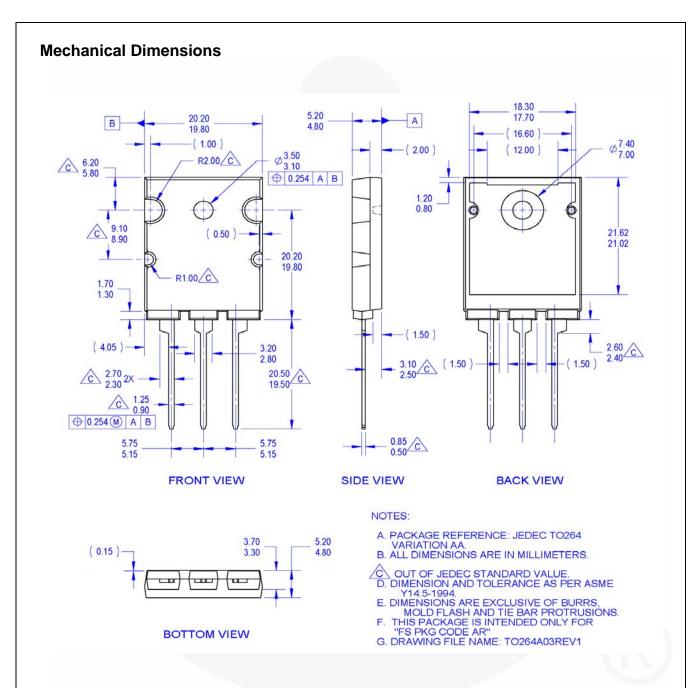


Figure 22. TO-264 3L - 3LD; TO264; MOLDED; JEDEC VARIATION AA

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